

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	6397	electron beam evaporation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:25
S2	229	S1 with glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/12 17:37
S3	7612	electron beam evaporation or e beam evaporation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:41
S4	225	S3 and hermetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/12 18:31
S5	10	S3 same hermetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/12 18:31
S6	3	"4104418".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/12 18:35
S7	3	("4104418").URPN.	USPAT	ADJ	ON	2005/10/12 18:36
S8	16	("3276902" "3801356" "3836393" "4104418" "4374391" "4407061").PN. OR ("4731293"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/10/12 18:52
S9	20	("2084747" "3432417" "3837866" "3885975" "3888685" "4091171").PN. OR ("4407061"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/10/13 11:30
S10	1866	electron beam (evaporation deposition) or e beam (evaporation or deposition) or e-beam (evaporation or deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:42
S11	10682	electron beam (evaporation or deposition) or e beam (evaporation or deposition) or e-beam (evaporation or deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 15:11

S12	1	S11 same negative resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:46
S13	113	S11 and negative resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:46
S14	1383	S11 same glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:46
S15	6	S14 and negative resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 12:35
S16	80	427/473.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 11:54
S17	248	427/504.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 12:34
S18	1189	427/585.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 12:34
S19	438	S14 and \$5resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 12:35
S20	152	S14 same \$5resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 12:35
S21	10682	electron beam (evaporation or deposition) or e beam (evaporation or deposition) or e-beam (evaporation or deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 15:12

S22	1084	S21 same (metal\$3 near5 (substrate or surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 15:14
S23	230	S22 same glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 16:05
S24	149	S21 same (metal\$3 (substrate or surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 16:06
S25	7	S24 same glass	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 15:14
S26	1018	S21 with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 16:06
S27	24	S26 same (metal\$3 (substrate or surface))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/13 16:06
S28	20	("4617192" "4749255").PN. OR ("5451548").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2005/10/14 11:06
S31	107	plasma ion assisted deposition or PIAD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:30
S33	7	S31 same (glass or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 11:12
S34	107	plasma ion assisted deposition or PIAD or plasma ion-assisted deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:31

S35	7	S34 same (oxide or glass or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:36
S36	20999	evaporation with (oxide or glass or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:43
S37	49	S36 with metal\$3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:43
S38	3	S37 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:37
S39	19	S37 and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:44
S40	3	S39 and (chemical mechanical polishing or cmp)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:38
S41	40042	evaporat\$3 with (oxide or glass or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:30
S42	98	S41 with metal\$3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:31
S43	42	S42 and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:44
S44	23	S43 not S39	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 14:44

S45	40908	evaporat\$3 with (oxide or glass or dielectric or silicate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:30
S46	4925	S45 with (copper or aluminum or tungsten or metal\$3 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:32
S47	130	S45 with ((copper or aluminum or tungsten or metal\$3) substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:33
S48	16	S47 and planar\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:37
S49	2	"4827870".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:38
S50	2	"4793980".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 15:59
S51	16	dielectric over metal and cmp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:12
S52	46	resistor same platinum same passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:14
S53	1	S52 and cmp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:13
S54	1252	resistor same platinum same (passivat\$3 or barrier or dielectric or oxide or glass)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:15

S56	0	S54 same (cmp or chemical mechanical polishing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:23
S57	28	S54 and (cmp or chemical mechanical polishing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:15
S58	149	S54 same etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:23
S59	16	S58 same evaporat\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 16:23
S60	5	("5543775").URPN.	USPAT	ADJ	ON	2005/10/14 18:08
S61	113	electron beam evaporation and moving substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:25
S62	11	electron beam evaporation same moving substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:38
S63	3	cmp passivation layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:39
S64	692	cmp same passivation layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:40
S65	372	cmp with passivation layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/10/14 18:40